

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

#6/A
4-12-02
Mullish

In re the Application of: NIHEI, MITZUHASHI et al

Serial No.: 09/746,064

Filed: December 26, 2000

For: SEMICONDUCTOR TRIODE DEVICE HAVING
A COMPOUND-SEMICONDUCTOR CHANNEL LAYER



Group Art Unit: 2815

Examiner: BAUMEISTER, Bradley W

2000 MAIL ROOM

APR -9 2002

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AMENDMENT UNDER 37 CFR §1.111

Commissioner for Patents
Washington, D.C. 20231

April 5, 2002

Sir:

In response to the Office Action dated December 6, 2001, extended to April 6, 2002 by a one month Petition for Extension of Time, please amend the above-identified application as follows:

IN THE SPECIFICATION:

The paragraph beginning at page 14, line 7, has been replaced with the following,
rewritten paragraph:

A1 -- In the structure of FIG. 9A, a gate electrode 63 of WSi is formed on the TiO₂
film 62 with a thickness or height of about 300nm.--

The paragraph beginning at page 14, line 10 has been replaced with the following,
rewritten paragraph:

A2 -- Next, in the next step of FIG. 9B, an ion implantation process of Si⁺ is conducted into the
GaAs substrate 61 while using the gate electrode 63 as a self-alignment mask, and n⁻-type LDD
regions 61B and 61C are formed in the substrate 61 at both lateral sided of the WSi gate electrode
63.--